

Docket No. 249979US2S/ams



*ITW*

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yuui SHIMIZU

SERIAL NO: 10/792,324

GAU:

FILED: March 4, 2004

EXAMINER:

FOR: SEMICONDUCTOR MEMORY DEVICE INCLUDING REFERENCE MEMORY CELL AND CONTROL METHOD

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,  
MAIER & NEUSTADT, P.C.

Marvin J. Spivak

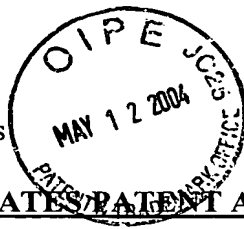
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**STATEMENT OF RELEVANCY**

**References AA, AW and AX on Form PTO-1449 are discussed in the specification.**

**Reference AO (JP 2009-242771) on Form PTO-1449:**

The proposed reference cell and scheme have applicability to the cross point cell architecture for MRAM. This reference is discussed in the specification.

Form PTO 1449  
(Modified)U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

249979US2S

SERIAL NO.

10/792,324

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Yuui SHIMIZU

FILING DATE

March 4, 2004

GROUP

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,081,445	06/27/2000	J. SHI, et al.			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

## FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	AO	2003-242771	08/29/2003	JAPAN		X
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

## OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

	AW	R. SCHEUERLEIN, et al., IEEE International Solid-State Circuits Conference, Digest paper, pages 128-129, "TA 7.2 A 10NS READ AND WRITE NON-VOLATILE MEMORY ARRAY USING A MAGNETIC TUNNEL JUNCTION AND FET SWITCH IN EACH CELL", 2000
	AX	M. DURLAM, et al., IEEE International Solid-State Circuits Conference, Digest Paper, pages 130-131, "TA 7.3 NONVOLATILE RAM BASED ON MAGNETIC TUNNEL JUNCTION ELEMENTS", 2000
	AY	
	AZ	

☐ Additional References sheet(s) attached

Examiner

Date Considered

\*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.